

Automotive Single-Channel Ultra-High-Speed GaN Predriver**Features**

- AEC-Q100 Grade-1 Qualified (TPM1025Q Only)
- 5-V Single Supply with Optimized Output Damping for GaN Reliability
- 7-A Peak Source and 5-A Sink-Drive Current
- 1-ns Minimum Input Pulse Width (Typical)
- Support 60-MHz Operating Frequency
- Low Propagation Delay
- Optimized Pinout for Nanosecond-pulse-width
- Fast Rise-and-Fall Times
- ESD Protection Exceeds JESD 22 – 2-kV HBM, 1-kV CDM
- Available in DFN2×2-6 and WLCSP Packages

Description

The TPM1020/TPM1025/TPM1025Q is a family of low-side single-channel and ultra-high-speed gate drivers for GaN and logic-level MOSFETs. It is optimized for high-speed applications such as Lidar and high-density power converters with enhanced low propagation delay design. The 0.85-mm × 1.25-mm WLCSP package of the TPM1020 and the 2-mm × 2-mm DFN package of the TPM1025 minimize parasitic inductance in the gate driver power loop.

Applications

- Laser Distance Measuring System
- Automotive Lidar
- Driver Monitoring System
- GaN DC/DC Conversion System

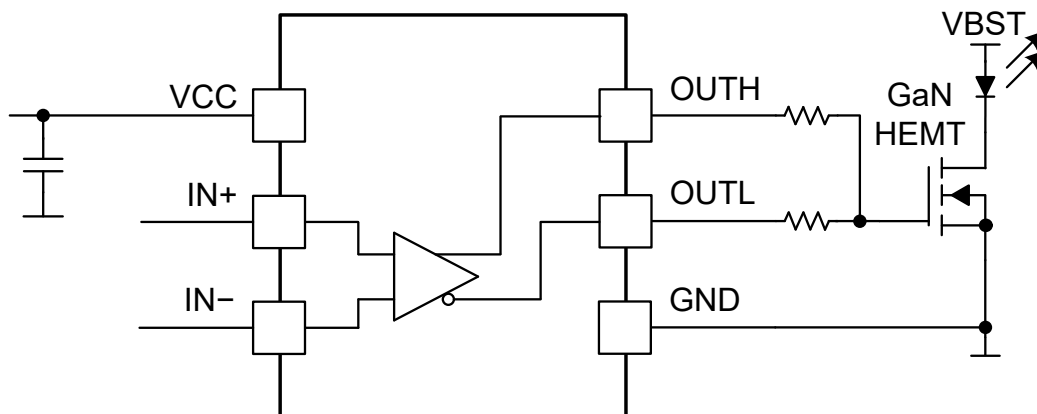
Typical Application Circuit

Table of Contents

Features	1
Applications	1
Description	1
Typical Application Circuit	1
Product Family Table	3
Revision History	3
Pin Configuration and Functions	4
Specifications	6
Absolute Maximum Ratings ⁽¹⁾	6
ESD, Electrostatic Discharge Protection.....	6
Recommended Operating Conditions.....	6
Thermal Information.....	7
Electrical Characteristics.....	8
Typical Performance Characteristics.....	10
Detailed Description	12
Overview.....	12
Functional Block Diagram.....	12
Feature Description.....	12
Application and Implementation	14
Application Information	14
Typical Application.....	14
Layout	17
Layout Guideline.....	17
Layout Example.....	17
Tape and Reel Information	18
Package Outline Dimensions	19
DFN2X2-6.....	19
WLP 0.85mm×1.25mm.....	20
Order Information	21
IMPORTANT NOTICE AND DISCLAIMER	22

Product Family Table

Order Number	Quality Grade	Package
TPM1020-WLPR	Industrial	WLCSP 0.85*1.25
TPM1025-DFOR	Industrial	DFN2X2-6
TPM1025Q-DFOR-S	Automotive	DFN2X2-6

Revision History

Date	Revision	Notes
2025-07-20	Rev.A.0	Initial release

Pin Configuration and Functions

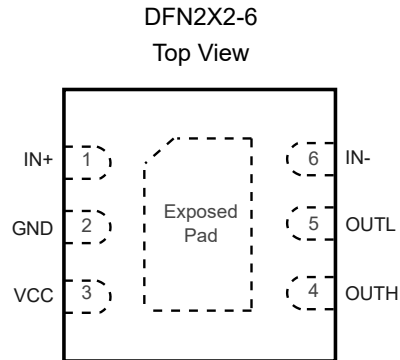


Table 1. Pin Functions: TPM1025

Pin No.	Pin Name	I/O	Description
1	IN+	I	Channel Positive Logic Input, Active High
2	GND	Ground	Device Ground
3	VCC	Supply	Device Supply
4	OUTH	O	Channel Pull-up Output
5	OUTL	O	Channel Pull-down Output
6	IN-	I	Channel Negative Logic Input, Active High
Exposed Pad	EP	G	Exposed Pad. Recommend to connect to GND.

Automotive Single-Channel Ultra-High-Speed GaN Predriver

WLCSP
Top View

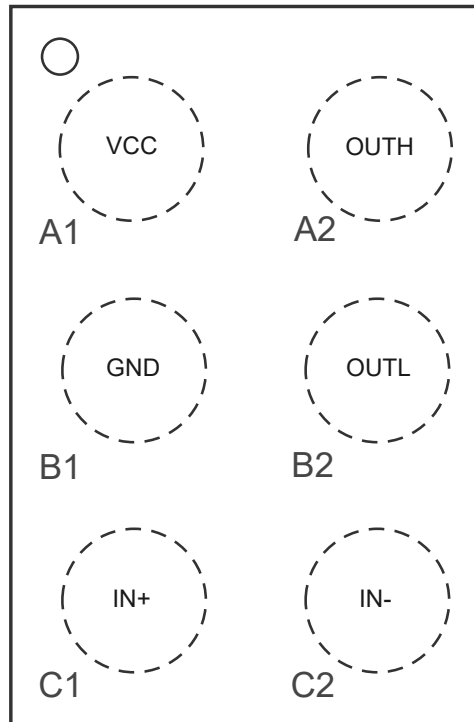


Table 2. Pin Functions: TPM1020

Pin No	Pin Name	I/O	Description
C1	IN+	I	Channel Positive Logic Input, Active High
B1	GND	Ground	Device Ground
A1	VCC	Supply	Device Supply
A2	OUTH	O	Channel Pull-up Output
B2	OUTL	O	Channel Pull-down Output
C2	IN-	I	Channel Negative Logic Input, Active High

Automotive Single-Channel Ultra-High-Speed GaN Predriver**Specifications****Absolute Maximum Ratings ⁽¹⁾**

Parameter		Min	Max	Unit
VCC	Power Supply Voltage, VCC	-0.3	+6	V
V _{OUTX}	Output Voltage Range OUTH, OUTL	-0.3	VCC + 0.3	V
	Output Voltage Range OUTH, OUTL, 5-ns Transient	-5	VCC + 5	V
	Output Voltage Range OUTH, OUTL, 10-ns Transient	-2	VCC + 2	V
V _{INX}	Input Voltage Range IN+, IN-	-0.3	6	V
I _{OUTX}	Continuous Output Channel Current OUTH	-500	+500	mA
	Pulsed Output Channel Sourcing Current OUTH (500 ns)		7	A
	Pulsed Output Channel Sinking Current OUTL (500 ns)		5	A
T _J	Operating Junction Temperature Range	-40	125	°C
T _{STG}	Storage Temperature Range	-65	150	°C
T _L	Lead Temperature (Soldering, 10 sec)		260	°C

- (1) Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. Exposure to any Absolute Maximum Rating condition for extended periods may affect device reliability and lifetime.
- (2) The inputs are protected by ESD protection diodes to each power supply. If the input extends more than 300 mV beyond the power supply, the input current should be limited to less than 10 mA.
- (3) Power dissipation and thermal limits must be observed.

ESD, Electrostatic Discharge Protection

Parameter		Condition	Minimum Level	Unit
HBM	Human Body Model ESD	ANSI/ESDA/JEDEC JS-001 , per AEC Q100-002	±2	kV
CDM	Charged Device Model ESD	ANSI/ESDA/JEDEC JS-002, per AEC Q100-011	±1	kV

Recommended Operating Conditions

Parameter		Min	Max	Unit
VCC	Power Supply Voltage, VCC	4.75	5.25	V
V _{INX}	Input Voltage IN+, IN-	0	VCC	V
V _{OUTX}	Output Voltage VOUTH, VOUTL	0	VCC	V
T _A	Operating Ambient Temperature Range	-40	125	°C

Automotive Single-Channel Ultra-High-Speed GaN Predriver**Thermal Information**

Package Type	θ_{JA}	θ_{JB}	θ_{JC}	Unit
DFN2X2-6	51.37	10.7	85.9	°C/W
WLCSP	133	38	1.7	°C/W

Automotive Single-Channel Ultra-High-Speed GaN Predriver

Electrical Characteristics

All test conditions: $V_{CC} = 5\text{ V}$, $T_J = -40\text{ }^{\circ}\text{C}$ to $150\text{ }^{\circ}\text{C}$, 1- μF capacitor between V_{CC} and GND, unless otherwise noted.

Parameter	Conditions	Min	Typ	Max	Unit
I_Q	VCC Quiescent Current $IN+ = H, IN- = L$			100	μA
I_{OP}	VCC Operating Current $f_{SW} = 30\text{ MHz}$, no load, $R_{OUTH} = 2\ \Omega$, $R_{OUTL} = 2\ \Omega$		40		mA
	$f_{SW} = 30\text{ MHz}$, 100-pF load, $R_{OUTH} = 2\ \Omega$, $R_{OUTL} = 2\ \Omega$		51		mA
V_{UVLO_rising}	Supply Under Voltage Lock Out Rising Threshold	3.92		4.35	V
V_{UVLO_hys}	Supply Under Voltage Lock Out Falling Hysteresis		85		mV
T_{OTP}	Over Temperature Shutdown, turn-off		170		$^{\circ}\text{C}$
ΔT_{OTP}	Over Temperature Hysteresis		20		$^{\circ}\text{C}$
V_{IN_H}	Input Signal High Threshold	1.7		2.6	V
V_{IN_L}	Input Signal Low threshold	1.1		1.8	V
V_{IN_HYS}	Input Hysteresis	0.38		1	V
$R_{IN+_pulldown}$	IN+ Pull-down Resistance	100	150	250	$\text{k}\Omega$
R_{IN-_pullup}	IN- Pull-up Resistance	100	150	250	$\text{k}\Omega$
C_{IN}	Input Capacitance		1.45		pF
V_{OL}	Output Low Voltage. OUTxL $I_{OUTL} = 100\text{ mA}$, $IN+ = 0\text{ V}$, $IN- = 5\text{ V}$			45	mV
$V_{CCx} - V_{OHx}$	Output High Voltage, OUTxH $I_{OUTH} = 100\text{ mA}$, $IN+ = 5\text{ V}$, $IN- = 0\text{ V}$			52	mV
I_{OH}	Output Peak Sourcing Current $V_{OUTH} = 0\text{ V}$, $IN+ = 5\text{ V}$, $IN- = 0\text{ V}$		7		A
I_{OL}	Output Peak Sinking Current $V_{OUTL} = 5\text{ V}$, $IN+ = 0\text{ V}$, $IN- = 5\text{ V}$		5		A
T_{start}	Startup Time, VDD Rising above UVLO $IN+ = VDD$, $IN- = 0\text{ V}$, VDD rising above UVLO to OUTH rising		40	78	μs
$T_{shut-off}$	ULVO Falling $IN+ = VDD$, $IN- = 0\text{ V}$, VDD falling below UVLO V to OUTH falling	0.7	2.5	3.5	μs
$T_{pd,r}^{(1)}$	Propagation Delay, Turn on $IN+$ to OUTH, $IN- = 0\text{ V}$, 100-pF load	1.5	2.6	4.1	ns
$T_{pd,f}^{(1)}$	Propagation Delay, Turn off $IN+$ to OUTL, $IN- = 0\text{ V}$, 100-pF load	1.8	2.9	4.4	ns
Δt_{pd}	Pulse Positive Distortion, ($t_{pd,r} - t_{pd,f}$)		300	610	ps
t_R	Output Rise-time 0- Ω series 220-pF load		650		ps

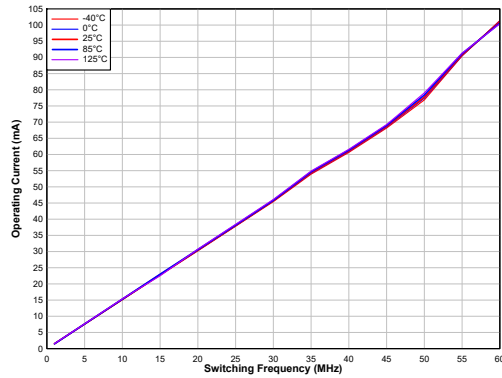
Automotive Single-Channel Ultra-High-Speed GaN Predriver

Parameter		Conditions	Min	Typ	Max	Unit
t _F	Output Fall-time	0-Ω series 220-pF load		850		ps
t _{PW}	Minimum Input Pulse Width That Changes Output State	0-Ω series 220-pF load		1.25		ns

(1) Guranteed by design.

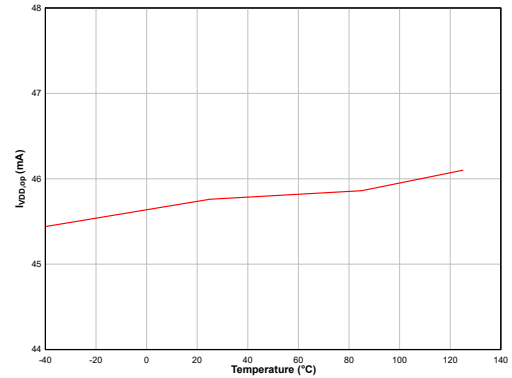
Typical Performance Characteristics

All test conditions: $V_{OUT} = 5\text{ V}$, $T_A = +25^\circ\text{C}$, unless otherwise noted.



2 Ω in series with 100-pF Load

Figure 1. Operating Current vs. Temperature



2 Ω in series with 100-pF Load, frequency = 30 MHz

Figure 2. Operating Current vs. Temperature

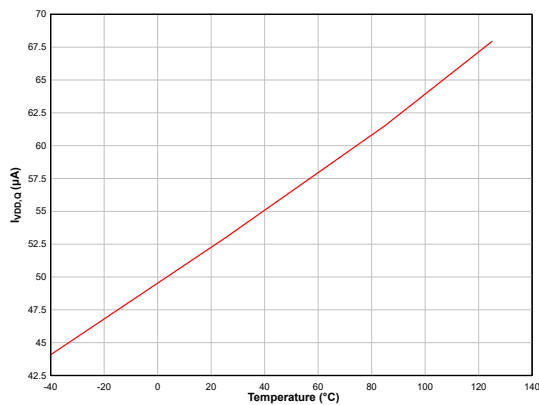
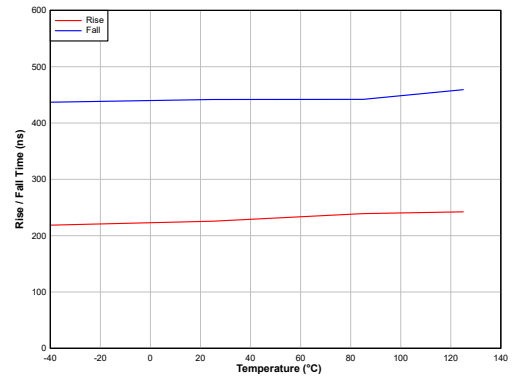
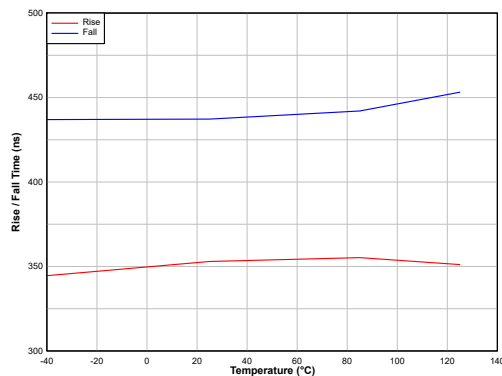


Figure 3. Quiescent current vs. Temperature



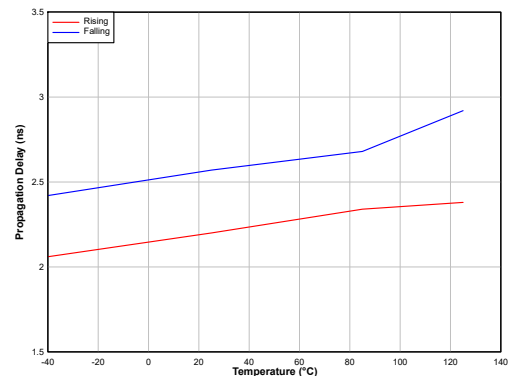
load = 220 pF

Figure 4. Rise & Fall time vs. Temperature



load = 1.8 nC

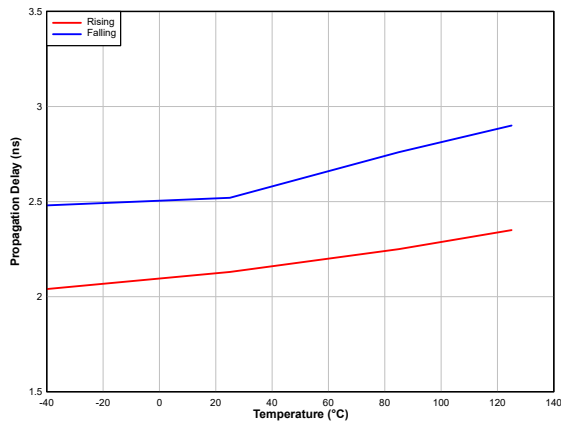
Figure 5. Rise & Fall time vs. Temperature



load = 100 nF

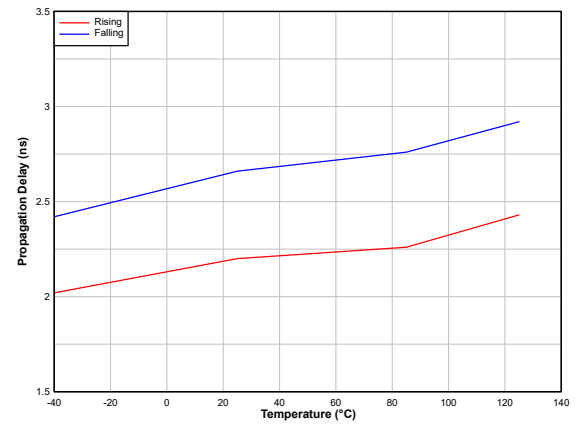
Figure 6. Propagation Delay vs. Temperature

Automotive Single-Channel Ultra-High-Speed GaN Predriver



load = 220 nF

Figure 7. Propagation Delay vs. Temperature



load = 1.8 pC

Figure 8. Propagation Delay vs. Temperature

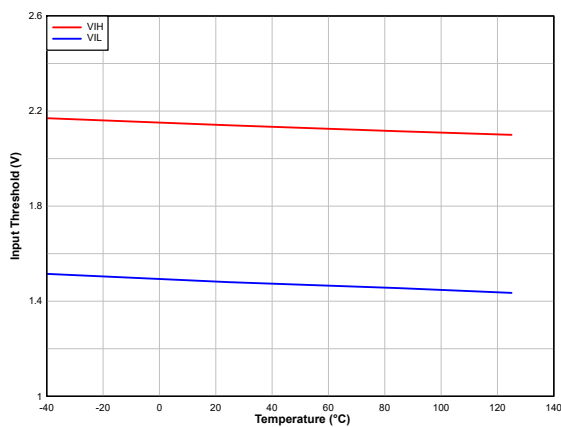


Figure 9. Input Threshold vs. Temperature

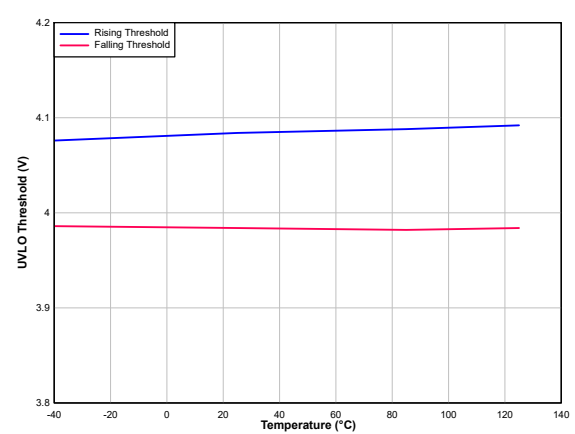
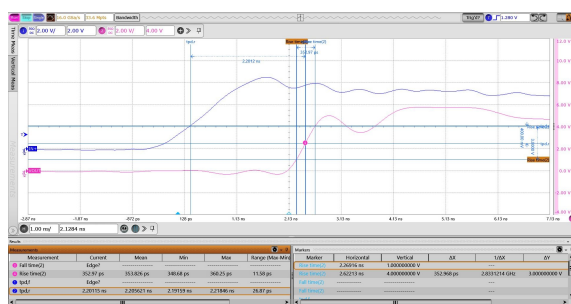
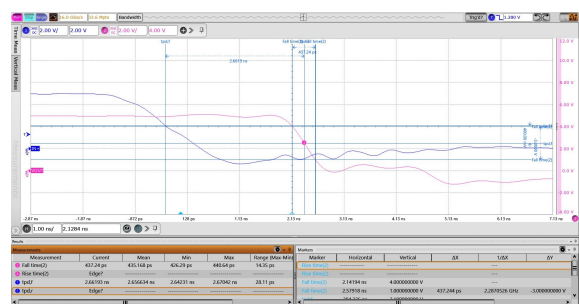


Figure 10. UVLO Threshold vs. Temperature



CH1: Input; CH2: GaN Transistor Gate

Figure 11. Rising Edge



CH1: Input; CH2: GaN Transistor Gate

Figure 12. Falling Edge

Detailed Description

Overview

The TPM1020/TPM1025/TPM1025Q is a family of low-side dual-channel and ultra-high-speed gate drivers for GaN and logic-level MOSFETs. It is optimized for high-speed applications such as Lidar and high-density power convertors with an enhanced low propagation delay design. The DFN2×2-6 package of the TPM1025 and the WLCSP package of the TPM1020 minimize parasitic inductance in the gate driver power loop and achieve state-of-the-art narrow pulse width.

Functional Block Diagram

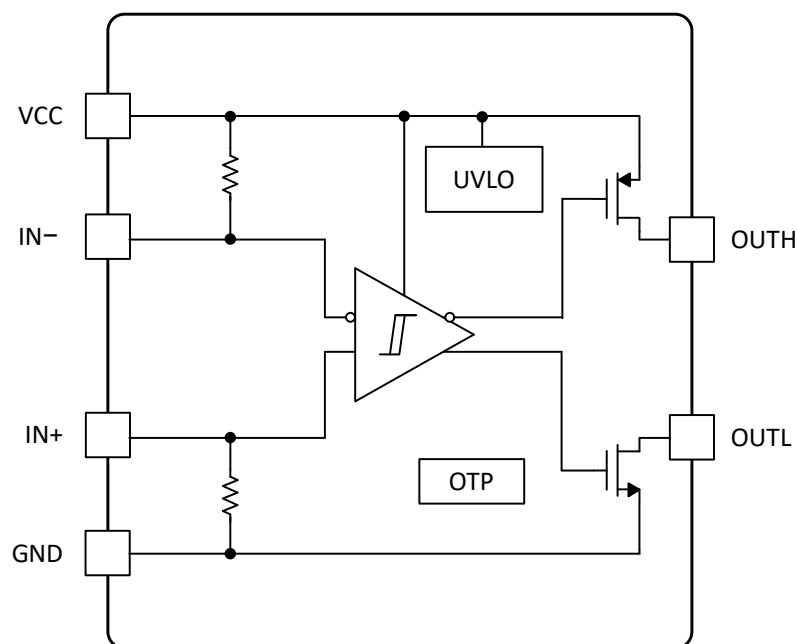


Figure 13. Functional Block Diagram

Feature Description

Supply and Under-Voltage-Lock-Out (UVLO)

The device has supply voltage under-voltage-lock-out (UVLO) monitors. When the supply voltage is above its rising threshold, the outputs are functional. When the supply voltage is below its falling threshold, the device pulls OUTL to GND. A short deglitch timer is inserted to avoid oscillations on the power supply.

Due to ultra-fast turn-on speed, channel output may drain high current on supply nodes within nanoseconds. 3PEAK recommends placing 3-terminal capacitors close to the device supply pins as low as possible. Parasitic inductance may prevent external capacitors from supplying current in such a short time.

Channel Input and Output

The channel inputs are connected to a low-latency Schmitt trigger. It can cut propagation delay without additional gates. The inputs are pulled low via internal resistors.

The TPM1025x provides split pull-up and pull-down paths. The split outputs allow users to independently configure pull-up and pull-down slew-rate via external resistors. The maximum output sink/source current is +7 A / -5 A. Configuring slew rates

Automotive Single-Channel Ultra-High-Speed GaN Predriver

may reduce ringing on GaN gate node due to parasitic inductance/capacitance, thus it can improve the reliability of GaN transistors.

Table 3. Output Truth Table

IN+	IN-	OUTH	OUTL
H	L	H	High-Impedance
L	H	High-Impedance	L
Floating (Internal Pull Down) or L	X	High-Impedance	L
X	Floating (Internal Pull Up) or H	High-Impedance	L

Over-Temperature Protection (OTP)

The TPM1025x provides an independent over-temperature protection function to independently disable each channel. When the junction temperature rises above the rising threshold, the channel outputs are disabled; when the junction temperature falls below the falling threshold, the channel outputs are enabled.

Application and Implementation

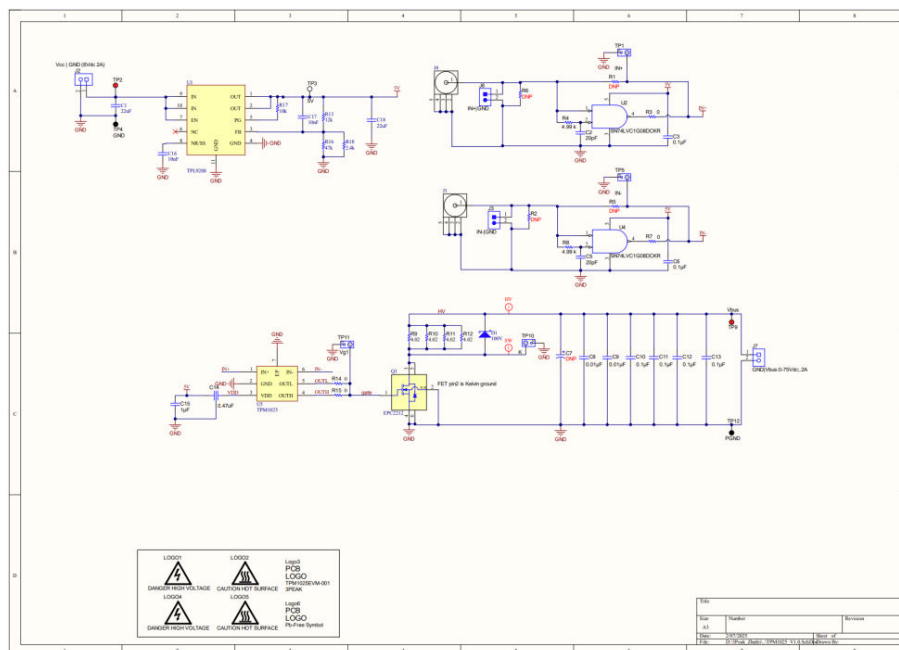
Note

Information in the following application sections is not part of the 3PEAK's component specification and 3PEAK does not warrant its accuracy or completeness. 3PEAK's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

Application Information

In a modern Time-of-Flight (ToF) LIDAR system, it is necessary to ensure a narrow laser pulse. Gallium nitride (GaN) transistors are widely used in the industry due to their high switching frequency. As depicted in the schematic below, it is required to keep the gate driver output loop as small as possible to minimize parasitic inductance.

Typical Application



Designator	Value	Description	Package	MFR	Part No.	Quantity
U5	TPM1025	Low Side GaN and MOSFET Driver	WSO6-6	3PEAK	TPM1025-DFOR	1
C1, C18	22uF	22uF/10V, 0805	0805	Murata	GRM21BR61A2 26ME51L	2
C2, C5	20 pF	CAP, CERM, 20 pF, 50 V, +/- 5%, C0G/NP0, 0402	0402	Murata	GRM1555C1H2 00JA01D	2

Automotive Single-Channel Ultra-High-Speed GaN Predriver

Designator	Value	Description	Package	MFR	Part No.	Quantity
C3, C6	0.1uF	CAP, CERM, 0.1uF, 25V, +/-10%, X7R, 0603	0603	Murata	GRM188R71E1 04KA01D	2
C7	4.7 μ F	CAP, AL, 4.7 μ F, 100 V, +/- 20%, SMD	SMD,D8*L6.2m m	Nichicon	UUX2A4R7MC L1GS	0
C8, C9	0.01 μ F	CAP, CERM, 0.01 μ F, 100 V, +/- 1%, C0G/ NP0, 0805	0805	KEMET	C0805C103F1 GACTU	2
C10, C11, C12, C13	0.1 μ F	CAP, CERM, 0.1 μ F, 100 V, +/- 10%, X7R, 0603	0603	Murata	GRM188R72A1 04KA35D	4
C14	470nF	CAP, CERM, 0.1 μ F, 100 V, +/- 10%, X7R, 0603	0603	Murata	NFM18PC474R 0J3	1
C15	LWK107BJ225 MV	CAP, CERM, 1 μ F, 10 V, +/- 20%, X5R, 0306	0306	TAIYO YUDEN	LWK107BJ105 MV	1
C16, C17	10nF	CAP, CERM, 10nF, 25 V, +/- 5%, X7R, 0603	0603	Murata	GRT1885C1E1 03JA02D	2
D1	Schottky Diode	Diode, Schottky, 100 V, 2 A, PowerDI123	SOD-123FL	DIODES	DFLS2100-7	1
Q1	GaN	GANFET N-CH, 100V, 18A DIE	SMD	EPC	EPC2212	1
R1, R5	DNP	RES, 10, 5%, 0.063 W, 0402	0402	VISHAY	CRCW040210R 0JNED	0
R2, R6	DNP	RES, 50, 1%, 0.1 W, 0603	0603	VISHAY	CRCW060350R 0FKEA	0
R3, R7	0	RES, 0, 5%, 0.063 W, 0402	0402	VISHAY	CRCW0402000 0Z0ED	2
R4, R8	4.99 k	RES, 4.99 k, 1%, 0.1 W, 0603	0603	VISHAY	CRCW06034K9 9FKEA	2
R9, R10, R11, R12	4.02	RES, 4.02, 1%, 0.1 W, 0603	0603	VISHAY	CRCW06034R0 2FKEA	4

Automotive Single-Channel Ultra-High-Speed GaN Predriver

Designator	Value	Description	Package	MFR	Part No.	Quantity
R13	12k	RES, 12K, 1%, 0.1 W, 0603	0603	VISHAY	CRCW060312K 0FKAEC	1
R14, R15	0	RES, 0, 5%, 0.05 W, 0201	0201	PANASONIC	ERJ-1GE0R00 C	2
R16	47k	RES, 47K, 1%, 0.33 W, 0603	0603	VISHAY	CRCW060347K 0FKEAHP	1
R17	10k	RES, 10K, 1%, 0.1 W, 0603	0603	VISHAY	CRCW060310K 0FKEA	1
R18	2.4k	RES, 2.4K, 1%, 0.1 W, 0603	0603	VISHAY	CRCW06032K4 0FKEA	1
U1	TPL9208	2A Output, High-PSRR, Low-Noise LDO Regulator	DFNWB2P5*2P 5-10	3PEAK	TPL9208AD- DF5R-S	1
U2, U4	SN74LVC1G08 DCKR	Single 2-Input Positive-AND Gate	SOT23-5	TI	SN74LVC1G08 DCKR	2

Figure 14.

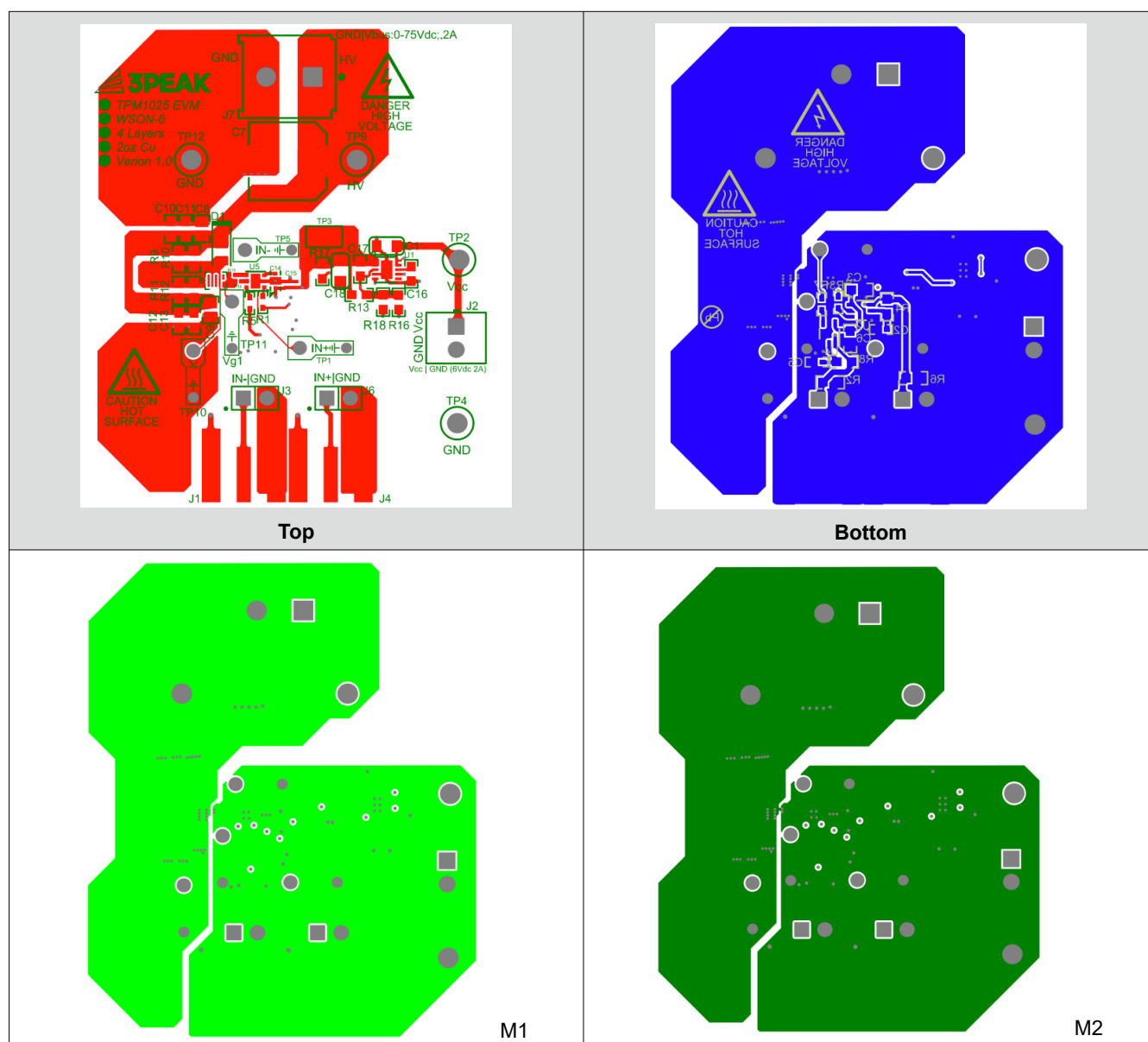
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Layout

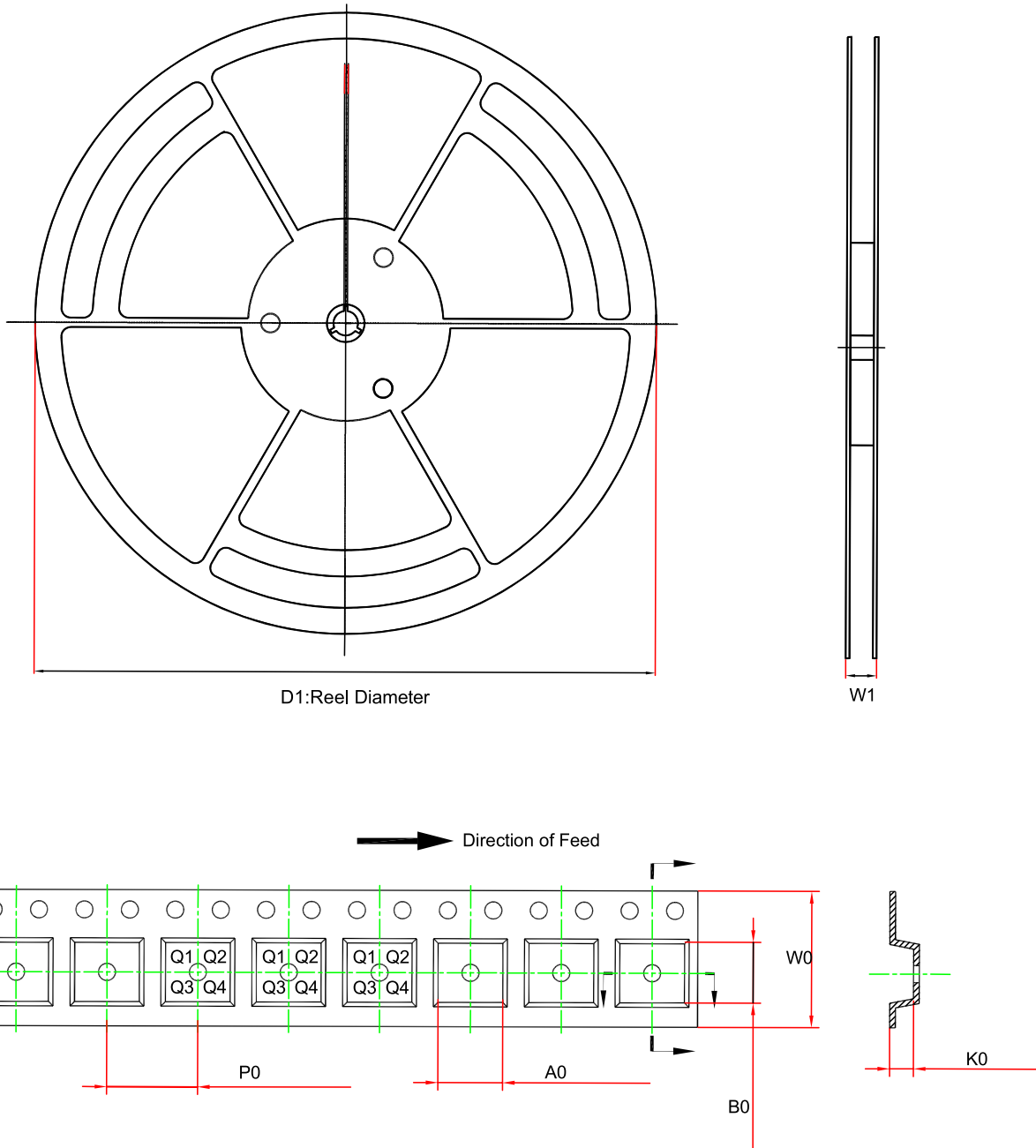
Layout Guideline

- Both input capacitors and output capacitors must be placed to the device pins as close as possible.
- It is recommended to bypass the input pin to ground with a 0.1- μ F bypass capacitor.
- It is recommended to use wide trace lengths or thick copper weight to minimize $I \times R$ drop and heat dissipation.
- Exposed pad must be connected to the PCB ground plane directly, the copper area must be as large as possible.

Layout Example



Tape and Reel Information

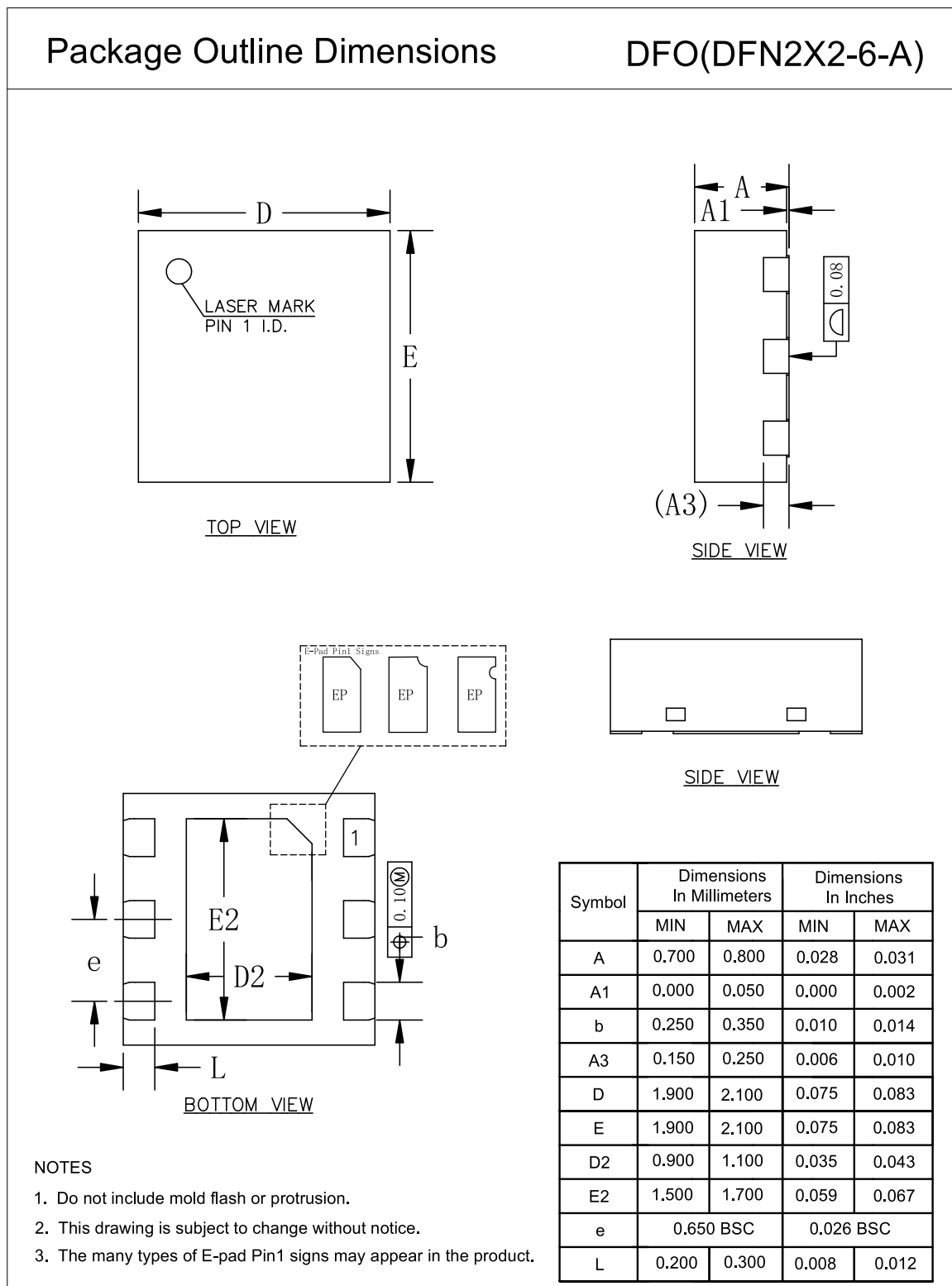


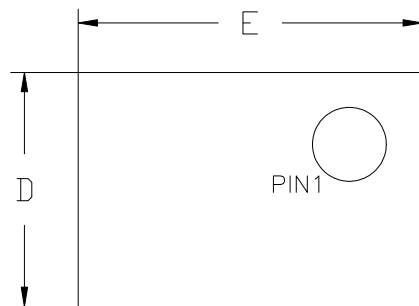
Order Number	Package	D1 (mm)	W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P0 (mm)	W0 (mm)	Pin1 Quadrant
TPM1025Q-DFOR-S	DFN2X2-6	180	12.5	2.3	2.3	1.0	4	8	Q1
TPM1025-DFOR	DFN2X2-6	180	12.5	2.3	2.3	1.0	4	8	Q1
TPM1020-WLPR	WLCSP	178	12.5	0.99	3.5	0.69	4	8	Q1

Automotive Single-Channel Ultra-High-Speed GaN Predriver

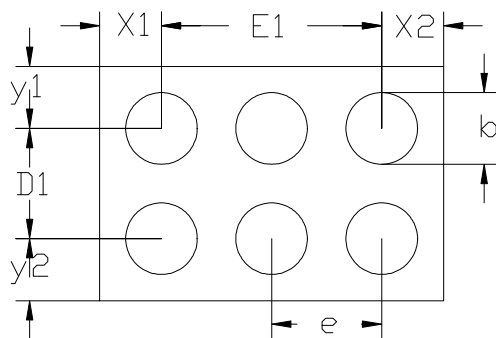
Package Outline Dimensions

DFN2X2-6

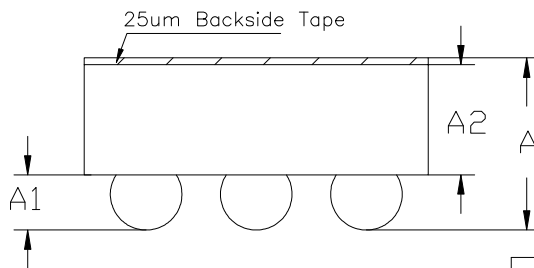


WLP 0.85mm×1.25mm
Package Outline Dimensions
WLP(WLCSP-A)


TOP VIEW
(MARK SIDE)



BOTTOM VIEW
(BALL SIDE)



SIDE VIEW

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	MIN	MAX	MIN	MAX
A	0.535	0.625	0.021	0.025
A1	0.180	0.220	0.007	0.009
A2	0.330	0.380	0.013	0.015
D	0.820	0.880	0.032	0.035
D1	0.400BSC		0.016	
E	1.220	1.280	0.048	0.050
E1	0.800BSC		0.031	
b	0.240	0.280	0.009	0.011
e	0.400BSC		0.016	
x1	0.225REF		0.009	
x2	0.225REF		0.009	
y1	0.225REF		0.009	
y2	0.225REF		0.009	

NOTES:

1. Do not include mold flash or protrusion.
2. This drawing is subject to change without notice.

Order Information

Order Number	Operating Ambient Temperature Range	Package	Marking Information	MSL	Transport Media, Quantity	Eco Plan
TPM1025Q-DFOR-S ⁽¹⁾	−40 °C to 125 °C	DFN2X2-6	Q15	MSL3	3000	Green
TPM1025-DFOR	−40 °C to 125 °C	DFN2X2-6	M15	MSL3	3000	Green
TPM1020-WLPR	−40 °C to 125 °C	WLCSP	2	MSL1	3000	Green

(1) Contact 3PEAK representatives for more information.

(2) The ambient temperature indicates the device operation condition range. Application thermal behavior needs to be taken care of when operating in high temperature scenarios.

Green: 3PEAK defines "Green" to mean RoHS compatible and free of halogen substances.

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